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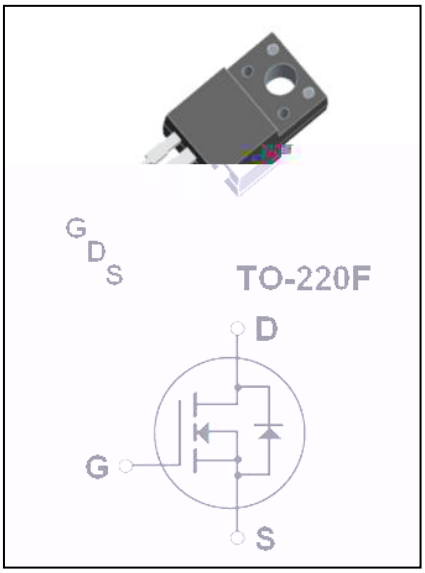

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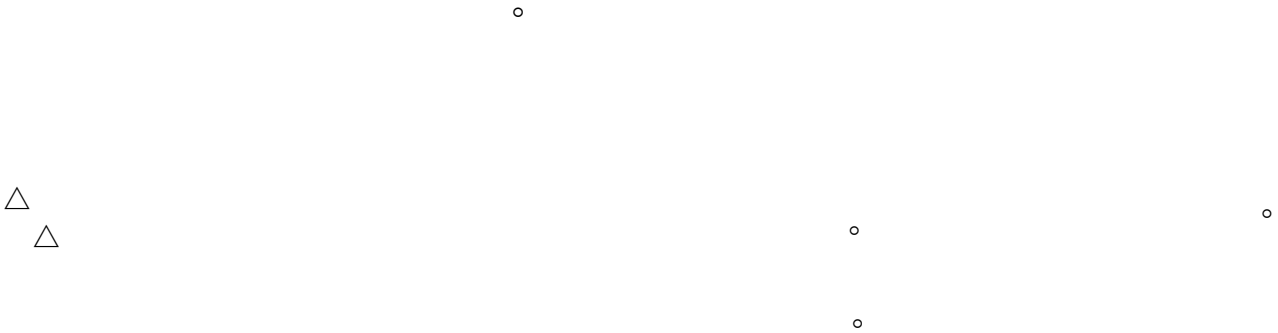
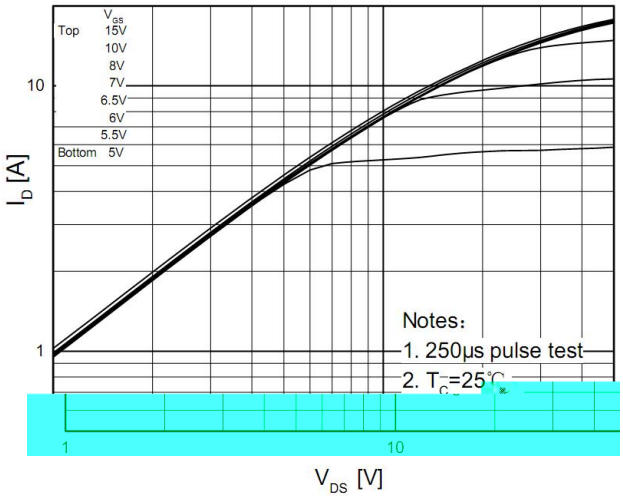
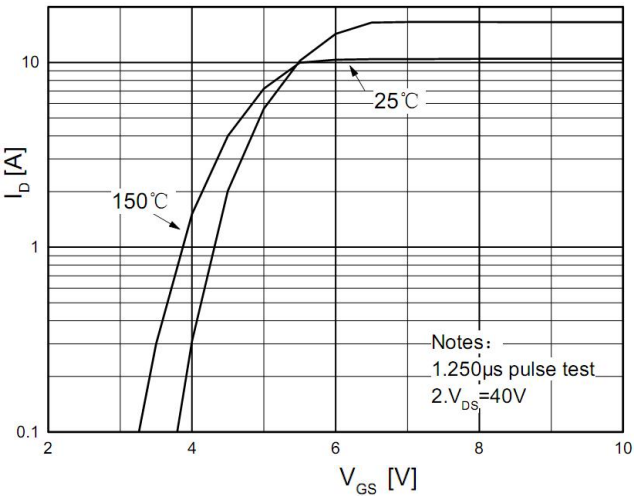
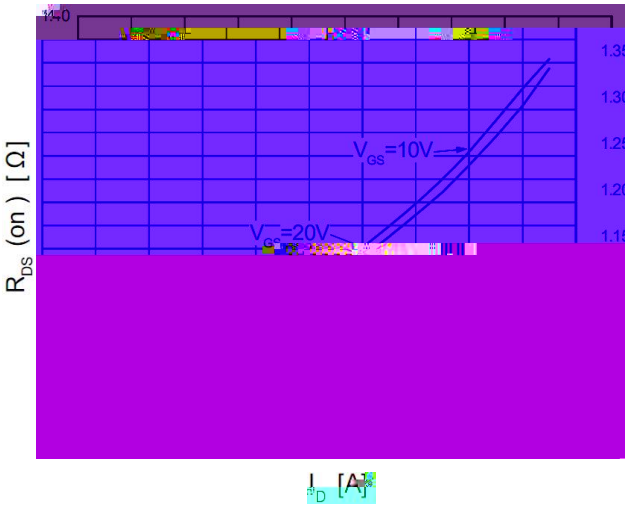
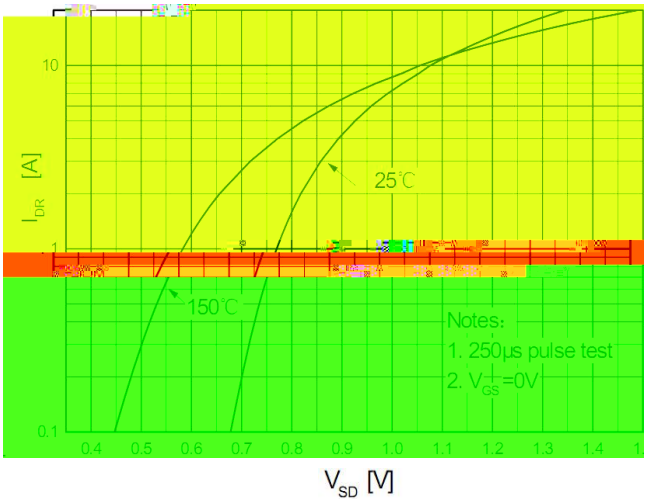
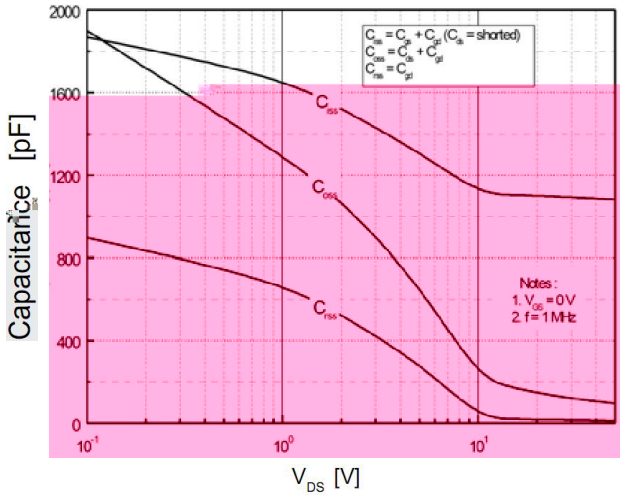


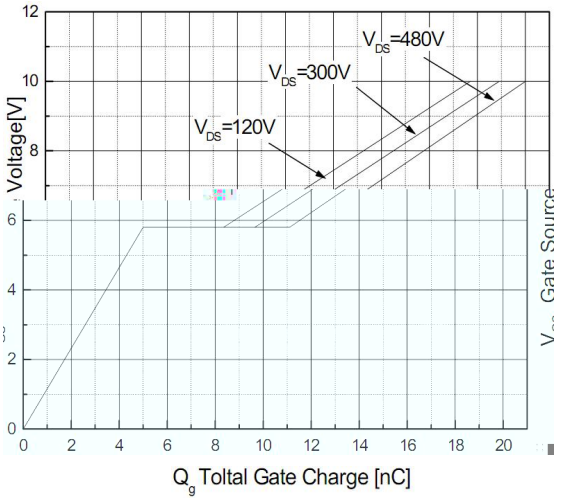

Top
V_{GS}
15V
10V
8V
7V
6.5V
6V
5.5V
Bottom 5V
Notes:
1. 250μs pulse test
2. T_C=25℃
I_D [A]
V_{DS} [V]

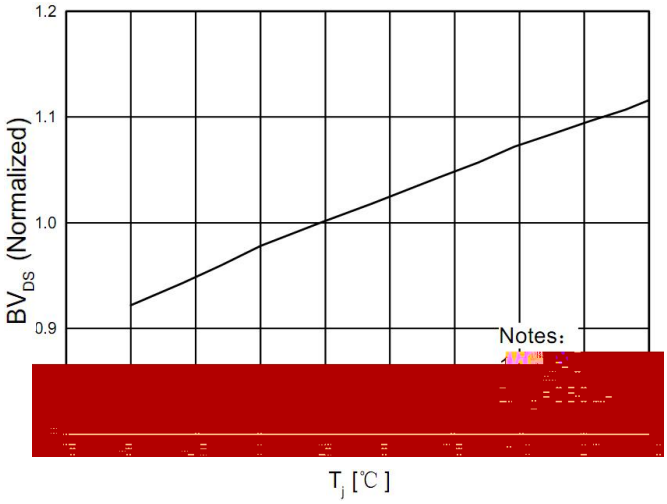

25℃
150℃
Notes:
1.250μs pulse test
2.V_{DS}=40V
I_D [A]
V_{GS} [V]

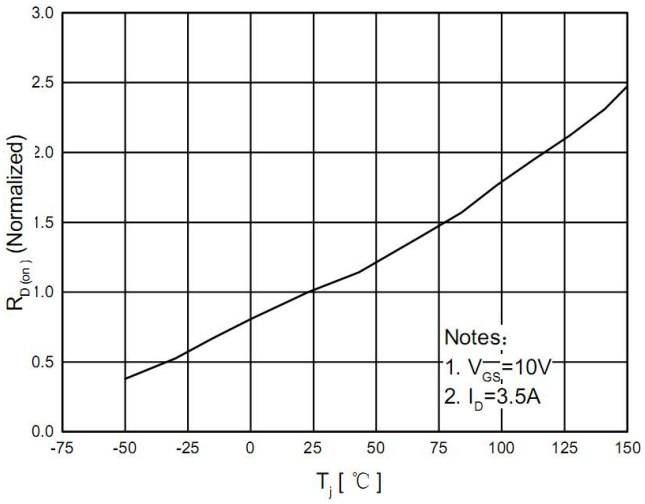

V_{GS}=10V
V_{GS}=20V
R_{DS} (on) [Ω]
I_D [A]

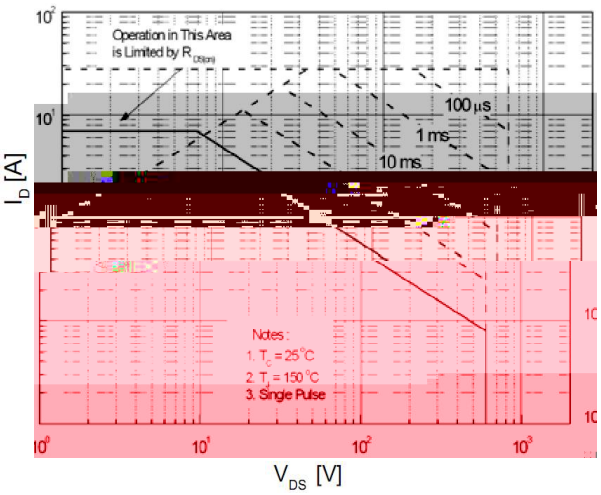

25℃
150℃
Notes:
1. 250μs pulse test
2. V_{GS}=0V
I_{DR} [A]
V_{SD} [V]

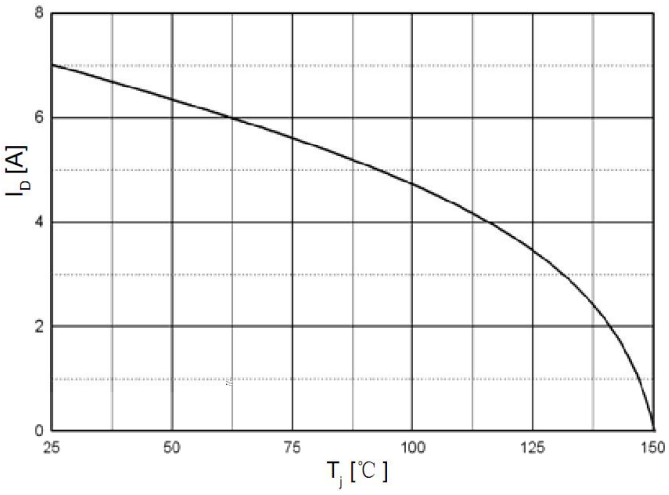

$C_{iss} = C_{gs} + C_{gd}$ (C_{ds} = shorted)
$C_{oss} = C_{ds} + C_{gd}$
$C_{rss} = C_{gd}$
C_{iss}
C_{oss}
C_{rss}
Notes:
1. V_{GS} = 0V
2. f = 1MHz
Capacitance [pF]
V_{DS} [V]


V_{DS}=480V
V_{DS}=300V
V_{DS}=120V
Voltage[V]
Gate Source
Q_g Toltal Gate Charge [nC]


1.2
1.1
1.0
0.9
BVDS (Normalized)
Notes:
Tj [℃]


3.0
2.5
2.0
1.5
1.0
0.5
0.0
RD(on) (Normalized)
Notes:
1. VGS=10V
2. ID=3.5A
-75
-50
-25
0
25
50
75
100
125
150
Tj [℃]


Operation in This Area
is Limited by RDS(on)
100 µs
1 ms
10 ms
ID [A]
Notes:
1. Tc = 25℃
2. Tj = 150℃
3. Single Pulse
VDS [V]


8
6
4
2
0
ID [A]
25
50
75
100
125
150
Tj [℃]

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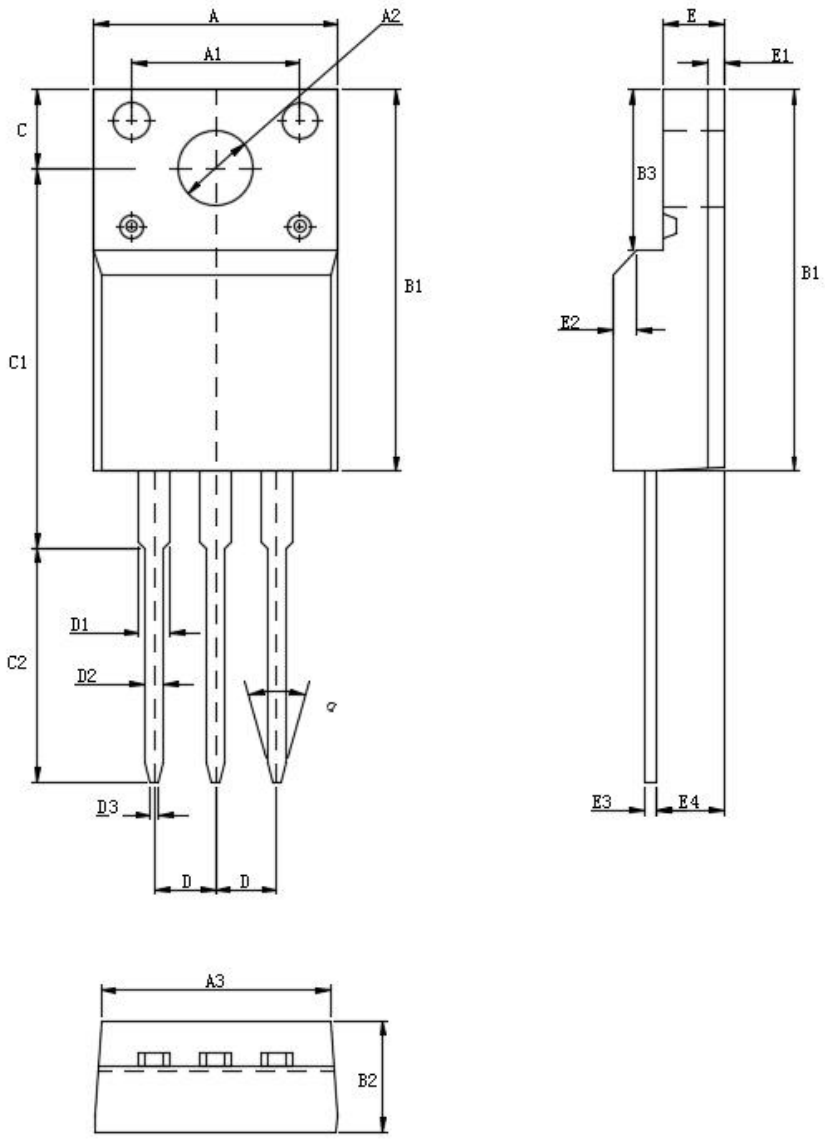
A
A2
A1
C
B1
C1
D1
C2
D2
D3
D
D
E
E1
B3
B1
E2
E3
E4
A3
B2